UNIKC
Semiconductor

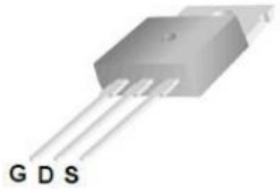
RoHS Compliant

P0806ATX

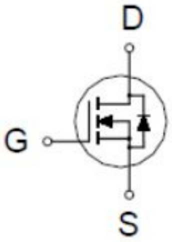
N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
60V	8mΩ @V_{GS} = 10V	110A



TO-220



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current[1]	T_C = 25 °C	I_D	110	A
	T_C = 100 °C		69	
Pulsed Drain Current[2]		I_{DM}	300	
Avalanche Current		I_{AS}	102	
Avalanche Energy	L = 0.1mH	E_{AS}	525	mJ
Power Dissipation	T_C = 25 °C	P_D	166	W
	T_C = 100 °C		66	
Operating Junction & Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		0.75	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

[1] Limited by maximum junction temperature.

[2] Limited by package.

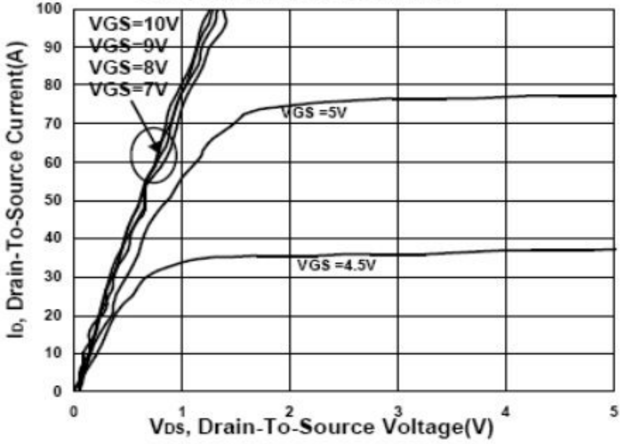
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60V, V_{GS} = 0V			1	μA
		V_{DS} = 48V, V_{GS} = 0V , T_J = 125 °C			25	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = 10V, V_{GS} = 10V	100			A
Drain-Source On-State	$R_{DS(ON)}$	V_{GS} = 10V, I_D = 55A		6.9	8	mΩ
Forward Transconductance[1]	g_{fs}	V_{DS} = 50V, I_D = 55A		90		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		4470		nF
Output Capacitance	C_{oss}			1090		
Reverse Transfer Capacitance	C_{rss}			120		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		2		Ω
Total Gate Charge[2]	Q_g	V_{DS} = 30V, V_{GS} = 10V, ID = 50A		91		nC
Gate-Source Charge[2]	Q_{gs}			23		
Gate-Drain Charge[2]	Q_{gd}			33		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DD} = 15V, I_D ≅ 55A, V_{GS} = 10V, R_{GEN} = 6Ω		20		nS
Rise Time[2]	t_r			110		
Turn-Off Delay Time[2]	$t_{d(off)}$			50		
Fall Time[2]	t_f			65		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current[3]	I_S				110	A
Forward Voltage[1]	V_{SD}	I_F = 55A, V_{GS} = 0V			1.3	V
Reverse Recovery Time	t_{rr}	V_{GS} = 0V, I_F = 55A, dI_F/dt = 100A / μS		125		nS
Reverse Recovery Charge	Q_{rr}			260		nC

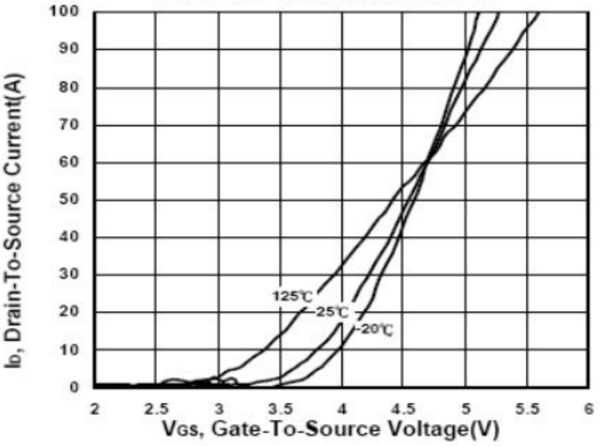
[1] Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

[2] Independent of operating temperature.

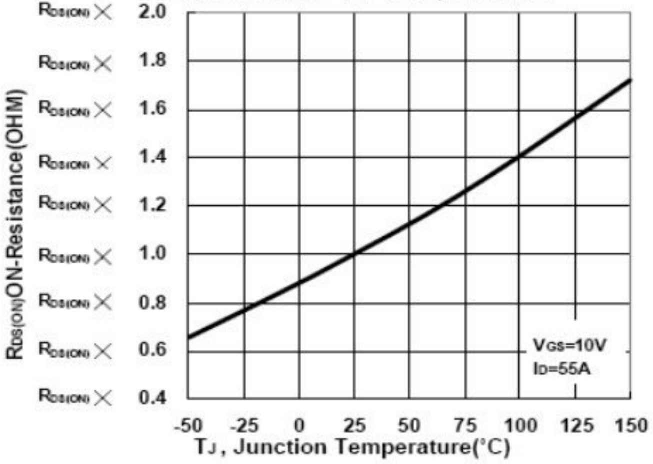
[3] Limited by maximum junction temperature.



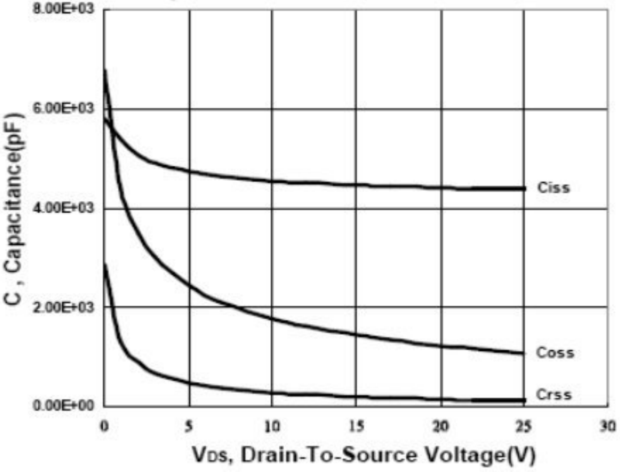
Output Characteristics



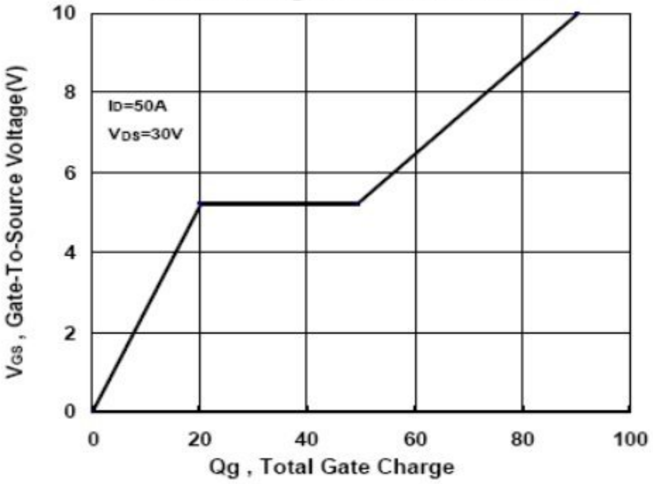
Transfer Characteristics



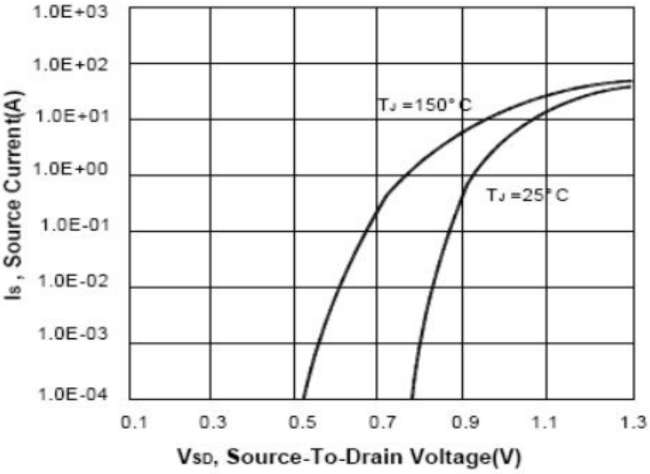
On-Resistance VS Temperature



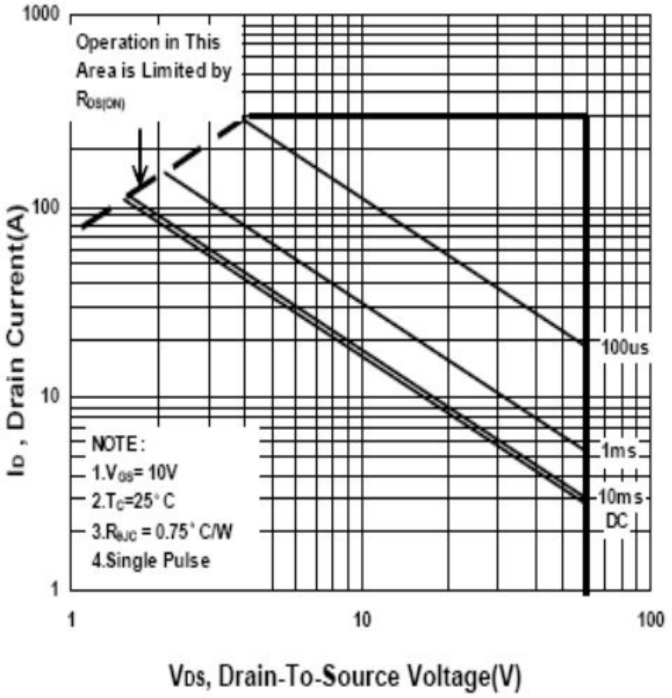
Capacitance Characteristic



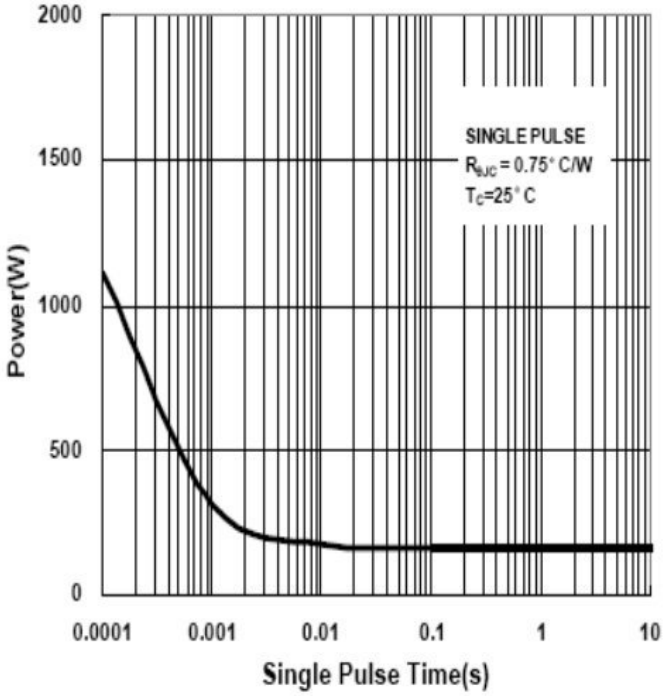
Gate charge Characteristics



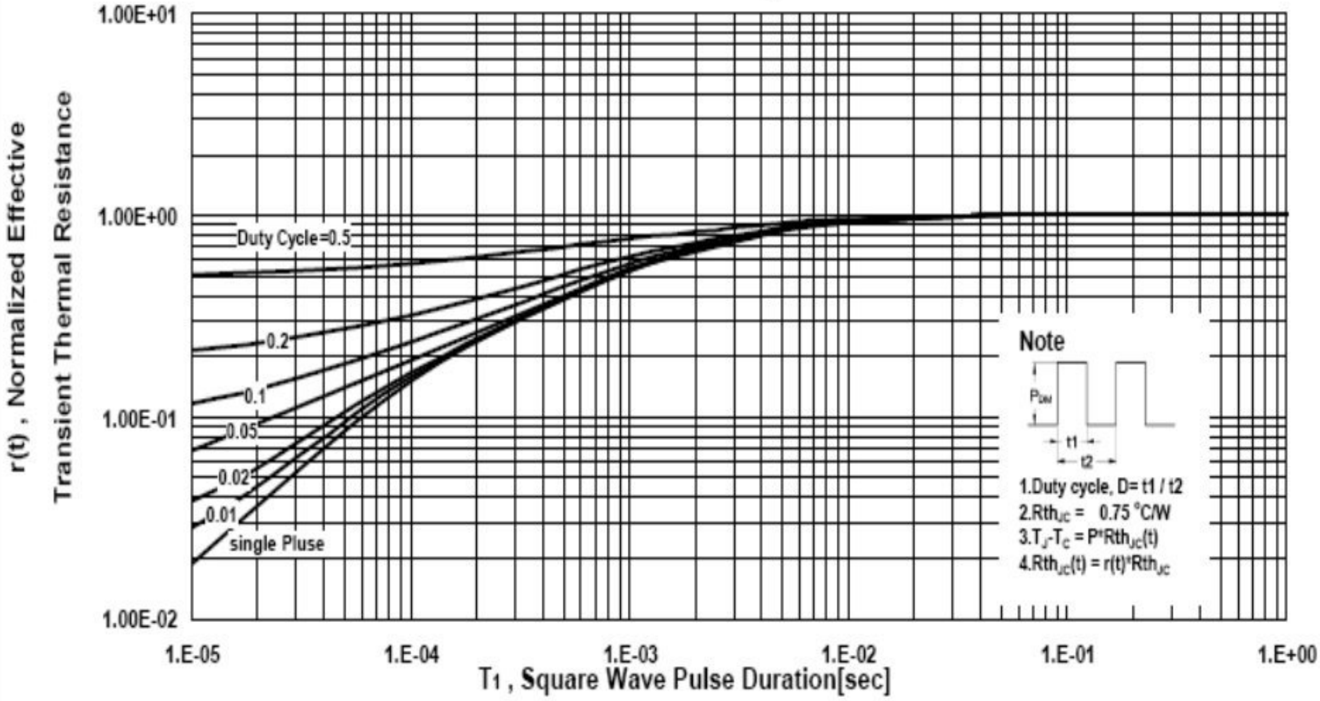
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

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Package Dimension

TO-220 (3-Lead) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	9.652	10.16	11.5	H	2.04	2.54	3.04
B	2.54	2.79	3.048	I	1.15	1.52	1.778
C	17.3		22.86	J	3.556	4.57	4.826
D	26.924	29.03	31.242	K	0.508	1.3	1.45
E	14.224	15.45	16.510	L	1.89	2.69	3.09
F	8.382	9.20	9.40	M	0.34	0.5	0.6
G	0.381	0.81	1.016	N